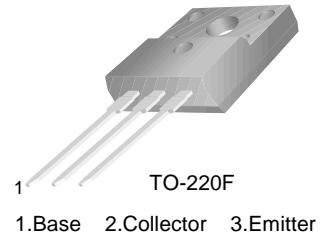




KSD2012

Low Frequency Power Amplifier

- Complement to KSB1366



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current	3	A
I_B	Base Current	0.3	A
P_C	Collector Power Dissipation ($T_C=25^\circ\text{C}$)	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 50\text{mA}$, $I_B = 0$	60			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 60\text{V}$, $I_E = 0$			100	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 7\text{V}$, $I_C = 0$			10	μA
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE} = 5\text{V}$, $I_C = 0.5\text{A}$ $V_{CE} = 5\text{V}$, $I_C = 3\text{A}$	100 20		320	
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C = 2\text{A}$, $I_B = 0.2\text{A}$		0.4	1	V
$V_{BE(\text{on})}$	Base-Emitter ON Voltage	$V_{CE} = 5\text{V}$, $I_C = 0.5\text{A}$		0.7	1	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 5\text{V}$, $I_C = 0.5\text{A}$		3		MHz

h_{FE} Classification

Classification	Y	G
h_{FE1}	100 ~ 200	150 ~ 320

Typical Characteristics

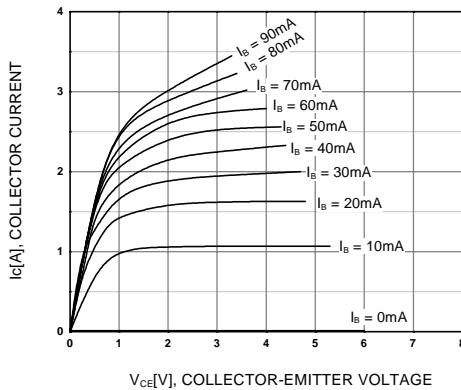


Figure 1. Static Characteristic

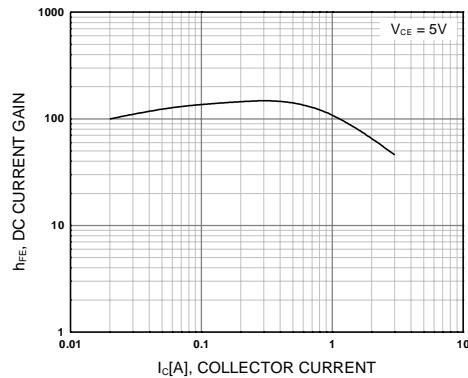


Figure 2. DC current Gain

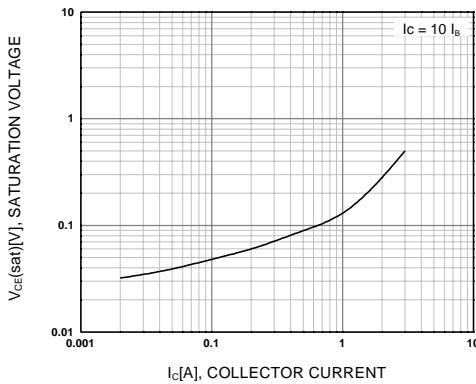


Figure 3. Collector-Emitter Saturation Voltage

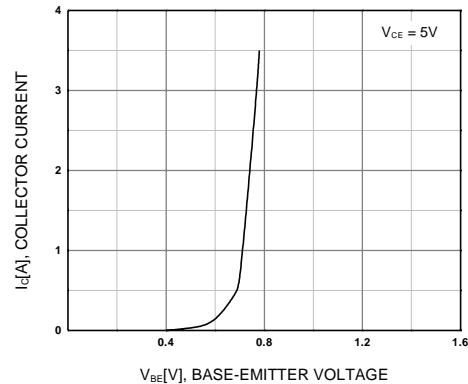


Figure 4. Base-Emitter On Voltage

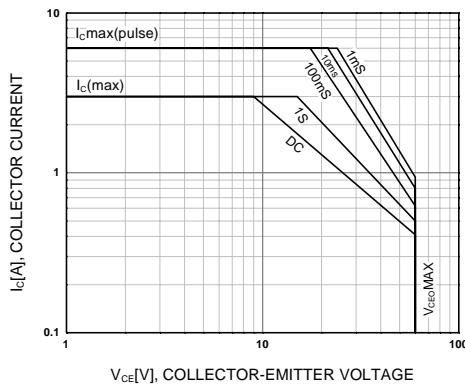


Figure 5. Safe Operating Area

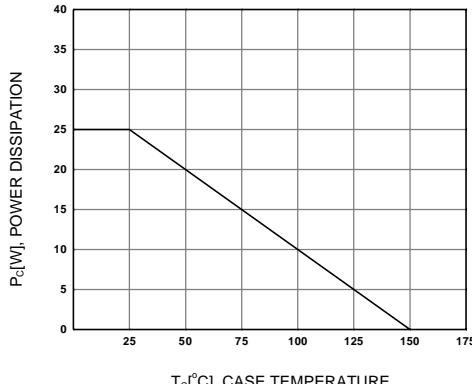


Figure 6. Power Derating

Package Demensions

TO-220F

